**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C                            |     | -   | -   | 30  | V    |
| V <sub>GS</sub>   | gate-source voltage              |   |     | -8  | -   | 8   | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | 900 | mA   |
| Static characte   | Static characteristics           |   |     |     |     | ,   |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 500 mA; $T_j$ = 25 °C   |     | -   | 370 | 490 | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



30 V, N-channel Trench MOSFET

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                       | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1   | G      | gate        | 1 🔲                                      | D<br>I         |
| 2   | S      | source      | 2 3                                      |                |
| 3   | D      | drain       | Transparent top view  DFN1006-3 (SOT883) | G S 017aaa255  |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package   | ıckage  |         |  |  |  |
|-------------|-----------|---|---------|--|--|--|
|             | Name      | Description   | Version |  |  |  |
| PMZ370UNE   | DFN1006-3 | DFN1006-3: leadless ultra small plastic package; 3 solder lands | SOT883  |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZ370UNE   | ZM           |

30 V, N-channel Trench MOSFET

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions  |     | Min | Max  | Unit |
|------------------|---------------------------------|---|-----|-----|------|------|
| $V_{DS}$         | drain-source voltage            | T <sub>j</sub> = 25 °C                              |     | -   | 30   | V    |
| $V_{GS}$         | gate-source voltage             |   |     | -8  | 8    | V    |
| I <sub>D</sub>   | drain current                   | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C   | [1] | -   | 900  | mA   |
|                  |                                 | V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C  | [1] | -   | 560  | mA   |
| I <sub>DM</sub>  | peak drain current              | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$ |     | -   | 3.6  | Α    |
| P <sub>tot</sub> | total power dissipation         | T <sub>amb</sub> = 25 °C                            | [2] | -   | 360  | mW   |
|                  |                                 |   | [1] | -   | 715  | mW   |
|                  |                                 | T <sub>sp</sub> = 25 °C                             |     | -   | 2700 | mW   |
| T <sub>j</sub>   | junction temperature            |   |     | -55 | 150  | °C   |
| T <sub>amb</sub> | ambient temperature             |   |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature             |   |     | -65 | 150  | °C   |
| Source-drain     | diode                           |   |     |     |      |      |
| I <sub>S</sub>   | source current                  | T <sub>amb</sub> = 25 °C                            | [1] | -   | 680  | mA   |
| ESD maximu       | m rating                        |   |     |     |      | ,    |
| V <sub>ESD</sub> | electrostatic discharge voltage | НВМ   | [3] | -   | 2000 | V    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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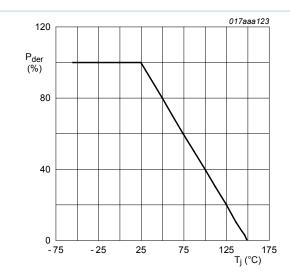


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

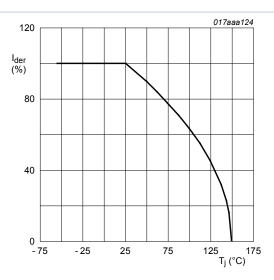


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

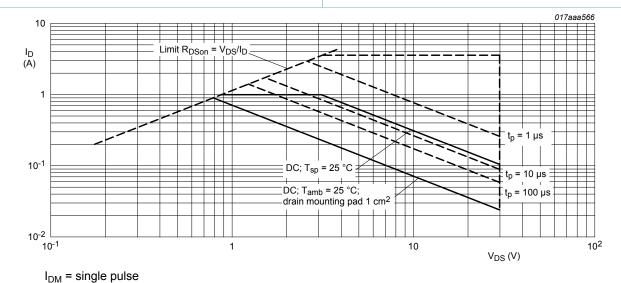


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol        | Parameter                | Conditions  |     | Min | Тур | Max | Unit |
|---------------|--------------------------|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance       | in free air | [1] | -   | 305 | 360 | K/W  |
|               | from junction to ambient |             | [2] | -   | 150 | 175 | K/W  |

PMZ370UNE

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| Symbol                | Parameter  | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|------|
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |            | -   | -   | 40  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

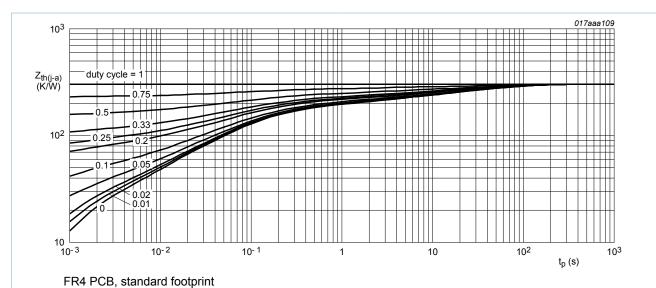


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

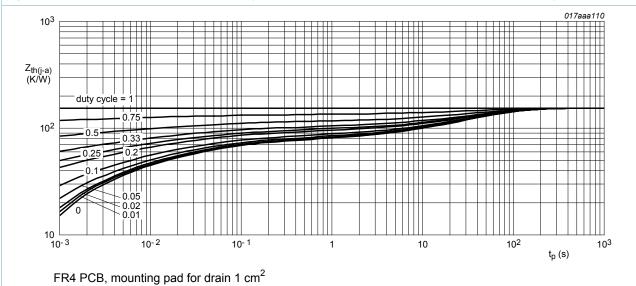


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

5/14

30 V, N-channel Trench MOSFET

## 10. Characteristics

### Table 7. Characteristics

| Symbol                        | Parameter                         | Conditions  | Min  | Тур  | Max  | Unit |
|-------------------------------|-----------------------------------|---|------|------|------|------|
| Static chara                  | acteristics                       |   | '    |      |      |      |
| $V_{(BR)DSS}$                 | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                              | 30   | -    | -    | V    |
| $V_{GSth}$                    | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                   | 0.5  | 0.77 | 1.05 | V    |
| I <sub>DSS</sub> drain leakaç | drain leakage current             | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -    | -    | 1    | μA   |
|                               |                                   | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C    | -    | -    | 10   | μA   |
| I <sub>GSS</sub>              | gate leakage current              | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -    | -    | 3    | μA   |
|                               |                                   | V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C     | -    | -    | 3    | μA   |
|                               |                                   | V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -    | -    | 0.5  | μA   |
|                               |                                   | V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C    | -    | -    | 0.5  | μA   |
| R <sub>DSon</sub>             | drain-source on-state             | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C  | -    | 370  | 490  | mΩ   |
|                               | resistance                        | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C | -    | 650  | 860  | mΩ   |
|                               |                                   | V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 400 mA; T <sub>j</sub> = 25 °C  | -    | 470  | 750  | mΩ   |
|                               |                                   | V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C  | -    | 630  | 1300 | mΩ   |
| g <sub>fs</sub>               | forward transconductance          | $V_{DS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C                            | -    | 1580 | -    | mS   |
| Dynamic ch                    | naracteristics                    |   | l    |      |      |      |
| Q <sub>G(tot)</sub>           | total gate charge                 | $V_{DS}$ = 15 V; $I_D$ = 500 mA; $V_{GS}$ = 4.5 V;                        | -    | 0.77 | 1.16 | nC   |
| Q <sub>GS</sub>               | gate-source charge                | T <sub>j</sub> = 25 °C  | -    | 0.15 | -    | nC   |
| $Q_{GD}$                      | gate-drain charge                 |   | -    | 0.16 | -    | nC   |
| C <sub>iss</sub>              | input capacitance                 | V <sub>DS</sub> = 25 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                 | -    | 52   | 78   | pF   |
| C <sub>oss</sub>              | output capacitance                | T <sub>j</sub> = 25 °C  | -    | 9    | -    | pF   |
| C <sub>rss</sub>              | reverse transfer capacitance      |   | -    | 3    | -    | pF   |
| t <sub>d(on)</sub>            | turn-on delay time                | $V_{DS}$ = 15 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 4.5 V;                 | -    | 11   | 22   | ns   |
| t <sub>r</sub>                | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                      | -    | 9    | -    | ns   |
| $t_{\text{d(off)}}$           | turn-off delay time               |   | -    | 54   | 108  | ns   |
| t <sub>f</sub>                | fall time                         |   | -    | 27   | -    | ns   |
| Source-drai                   | in diode                          |   | l l  |      |      | ,    |
| V <sub>SD</sub>               | source-drain voltage              | $I_S$ = 300 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C                             | 0.48 | 0.76 | 1.2  | V    |
|                               |                                   | 1   |      |      |      | _    |

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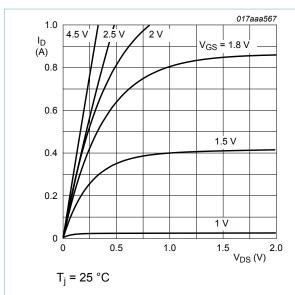


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

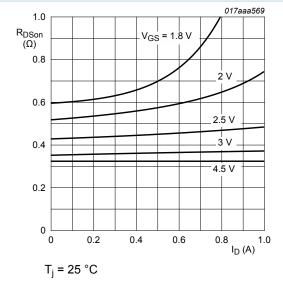


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

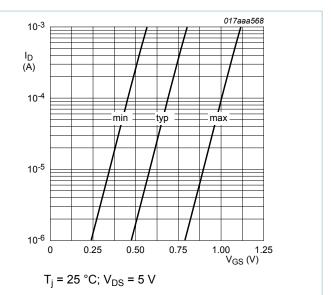


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

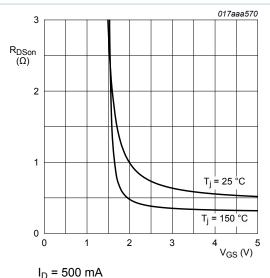


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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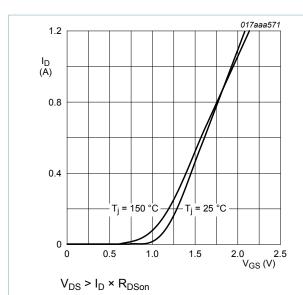


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

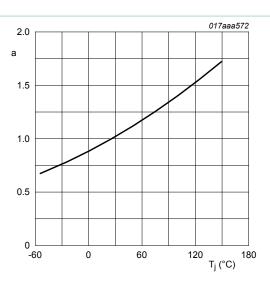


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

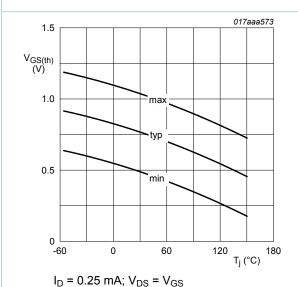


Fig. 12. Gate-source threshold voltage as a function of junction temperature

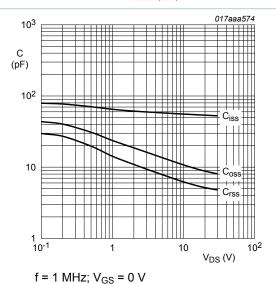
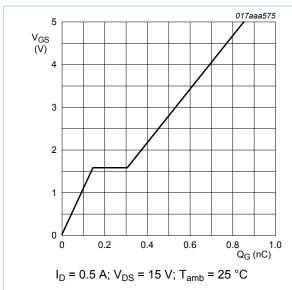


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, N-channel Trench MOSFET



V<sub>DS</sub>

V<sub>GS(pl)</sub>

V<sub>GS(th)</sub>

V<sub>GS</sub>

Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>GS</sub>
Q<sub>G(tot)</sub>

017aaa137

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

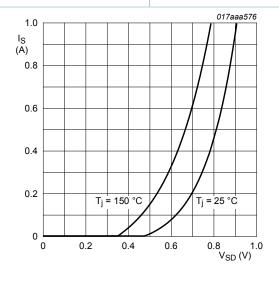
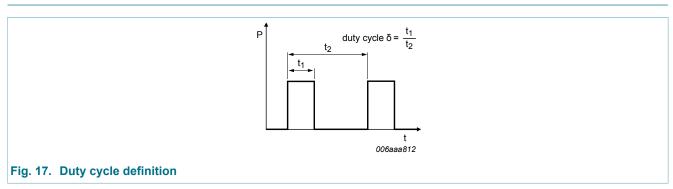


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



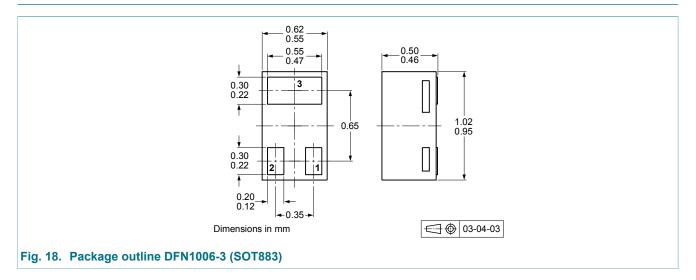
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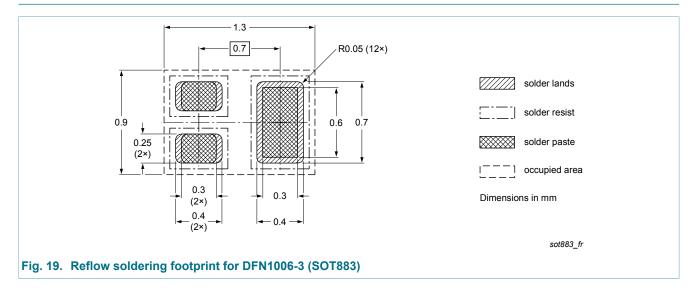
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## 12. Package outline



# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMZ370UNE v.1 | 20140514     | Product data sheet | -             | -          |

11 / 14

#### 30 V, N-channel Trench MOSFET

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|--------------------------------------|--------------------|---|
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### 30 V, N-channel Trench MOSFET

## 16. Contents

| 2 Features and benefits 3 Applications   | 1    | General description     | 1  |
|--|------|-------------------------|----|
| 4 Quick reference data   | 2    | Features and benefits   | 1  |
| 5 Pinning information  | 3    | Applications            | 1  |
| 6 Ordering information   | 4    | Quick reference data    | 1  |
| 7 Marking  | 5    | Pinning information     | 2  |
| 8 Limiting values  | 6    | Ordering information    | 2  |
| 9 Thermal characteristics  | 7    | Marking                 | 2  |
| 10 Characteristics   | 8    | Limiting values         | 3  |
| 11 Test information  | 9    | Thermal characteristics | 4  |
| 12 Package outline   | 10   | Characteristics         | 6  |
| 13 Soldering   | 11   | Test information        | 9  |
| 14 Revision history  | 12   | Package outline         | 10 |
| 15 Legal information  15.1 Data sheet status  15.2 Definitions  15.3 Disclaimers | 13   | Soldering               | 10 |
| 15.1 Data sheet status   | 14   | Revision history        | 11 |
| 15.2 Definitions   | 15   | Legal information       | 12 |
| 15.3 Disclaimers   | 15.1 | Data sheet status       | 12 |
|  | 15.2 | Definitions             | 12 |
| 15.4 Trademarks  | 15.3 | Disclaimers             | 12 |
|  | 15.4 | Trademarks              | 13 |

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14/14

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